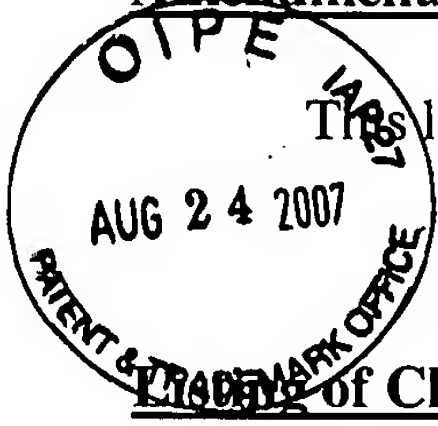


Amendments to the Claims:



This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A radiation-emitting semiconductor component comprising:

a semiconductor body comprising an active zone;

a patterned contact layer applied on a surface of the semiconductor body for electrical contact connection, wherein the patterned contact layer has a thickness which is less than 100 nm;

interspaces distributed over the patterned contact layer for the purpose of forming free areas on the surface which are not covered by the patterned contact layer; and

a mirror for covering the free areas.
2. (Currently Amended) The component according to claim 1, in which the mirror is embodied as a closed mirror layer covering the free areas and the patterned contact layer.
3. (Currently Amended) The component according to claim 2, in which the material of the patterned contact layer links electrically better to the semiconductor body than the material of the mirror layer.
4. (Currently Amended) The component according to claim 2, in which the material of the mirror layer reflects the radiation generated in the active zone better than the material of the patterned contact layer.

5. (Currently Amended) The component according to claim 1, in which the surface of the semiconductor body is formed by a p-doped layer made of a nitride compound semiconductor, and in which the material of the patterned contact layer forms an ohmic contact with respect to the surface.

6. (Currently Amended) The component according to claim 1, in which the patterned contact layer contains platinum or nickel.

7. (Previously Presented) The component according to claim 2, in which the mirror layer contains silver or aluminum.

8. (Canceled).

9. (Currently Amended) The component according to claim 1, in which the patterned contact layer comprises contact elements that are separated from one another, and in which a connecting layer for making contact among the contact elements is provided on the patterned contact layer.

10. (Previously Presented) The component according to claim 9, in which the contact elements have the form of cylinders.

11. (Previously Presented) The component according to claim 9, in which the contact elements are arranged at the nodes of a regular grid.

12. (Previously Presented) The component according to claim 11, in which the regular grid is a square grid.

13. (Previously Presented) The component according to claim 9, in which the surface of the semiconductor body is formed by a p-doped layer made of a nitride compound semiconductor, the p-doped layer having a surface which faces the active zone and constitutes an interface, wherein the distance between every two adjacent contact elements is related to the transverse conductivity of the p-doped layer such that the entire interface can be energized.

14. (Canceled)

15. (Previously Presented) The component according to claim 11, in which the regular grid is a hexagonal grid.

16. (Previously Presented) The component according to claim 1, in which the interspaces are filled with a filler in order to at least partially planarize the surface of the patterned contact layer.

17. (Previously Presented) The component according to claim 16, in which the filler contains an electrically conductive material.

18. (Previously Presented) The component according to claim 16, in which the filler contains a transparent and electrically insulating material.

19. (Previously Presented) The component according to claim 17, in which the filler contains zinc oxide or indium tin oxide.

20. (Previously Presented) The component according to claim 18, in which the filler contains SiO₂, a compound made of silicon and nitrogen or titanium oxide or plastic.

21. (Previously Presented) The component according to claim 16, in which the filler forms Bragg reflectors.

22. (Previously Presented) The component according to claim 21, in which the Bragg reflectors are produced from dielectrics.

23. (Previously Presented) The component according to claim 21, in which the Bragg reflectors are produced by epitaxy.

24. (Previously Presented) The component according to claim 1, in which the mirror is formed by Bragg reflectors arranged in the interspaces of the contact layer.

25. (Previously Presented) The component according to claim 24, in which the Bragg reflectors contain layer pairs lying one on top of the other, of which respectively one has a high refractive index and one has a low refractive index, and in which a number greater than 5 of layer pairs are provided in each Bragg reflector.

26. (Currently Amended) A radiation-emitting semiconductor component comprising:

a semiconductor body comprising an active zone;

a patterned contact layer applied on a surface of the semiconductor body for electrical contact connection, wherein the patterned contact layer comprises contact elements that are separated from one another, and wherein the contact elements have the ~~from~~ form of cylinders;

interspaces distributed over the patterned contact layer for the purpose of forming free areas on the surface which are not covered by the patterned contact layer; and

a mirror for covering the free areas.

27. (Currently Amended) A radiation-emitting semiconductor component comprising:

a semiconductor body comprising an active zone;

a patterned contact layer applied on a surface of the semiconductor body for electrical contact connection;

interspaces distributed over the patterned contact layer for the purpose of forming free areas on the surface which are not covered by the patterned contact layer, wherein the interspaces are filled with a filler in order to at least partially planarize the surface of the patterned contact layer, and wherein the filler contains a transparent and electrically insulating material; and

a mirror for covering the free areas.